

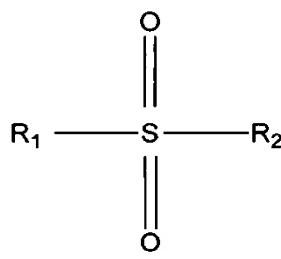
IN THE CLAIMS:

Please cancel claims 29 and 30.

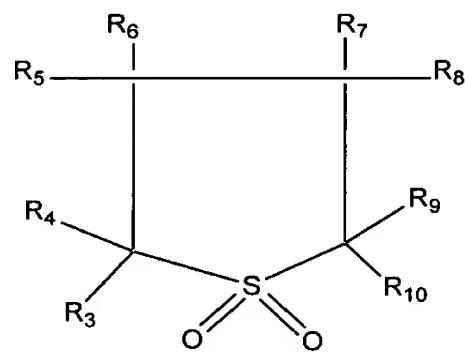
Rewrite the pending claims and add new claims as follows:

Claims 1-10 (canceled).

Claim 11. (currently amended) A method of removing a photoresist coating from a substrate using ~~the composition of claim 1~~ a composition comprising from about 0.01 percent by weight to about 10 percent by weight of one or more fluoride compounds, from about 15 percent by weight to about 50 percent by weight water, from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:



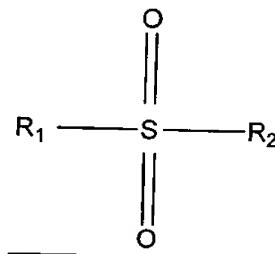
where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:



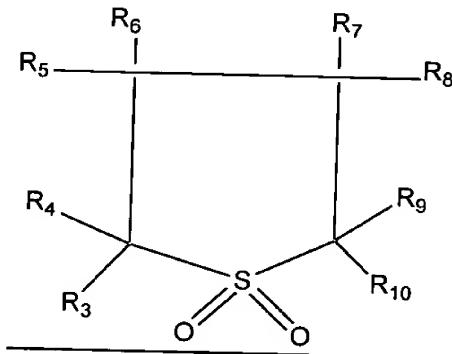
where R₃ - R₁₀ are independently H or an alkyl group, from about 0.1 to about 15 percent by weight of a basic amine compound, and a co-solvent selected from the group consisting of acetic acid, methyl acetate, methyl lactate, ethyl acetate, ethylene glycol diacetate, ethyl lactate, propylene glycol, propylene carbonate, N-methyl pyrrolidone, methoxyethoxyethanol and polyethylene glycol monolaurate.

Claim 12 (currently amended). A method of removing etch residue from a substrate using ~~the composition of claim 1~~ a composition comprising from about 0.01 percent by

weight to about 10 percent by weight of one or more fluoride compounds, from about 15 percent by weight to about 50 percent by weight water, from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:

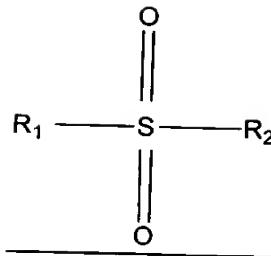


where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:

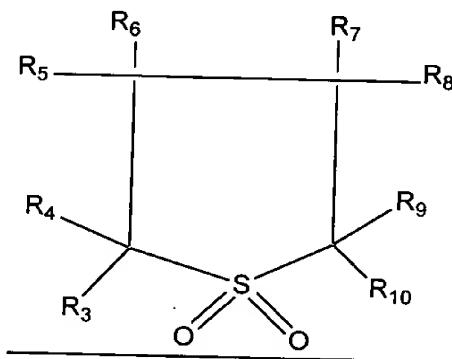


where R₃ - R₁₀ are independently H or an alkyl group, from about 0.1 to about 15 percent by weight of a basic amine compound, and a co-solvent selected from the group consisting of acetic acid, methyl acetate, methyl lactate, ethyl acetate, ethylene glycol diacetate, ethyl lactate, propylene glycol, propylene carbonate, N-methyl pyrrolidone, methoxyethoxyethanol and polyethylene glycol monolaurate.

Claim 13 (amended). A method of etching silicon oxide using ~~the composition of claim 1~~ a composition comprising from about 20 percent by weight to about 40 percent by weight of one or more fluoride compounds, from about 15 percent by weight to about 50 percent by weight water, from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:



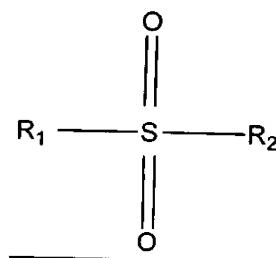
where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:



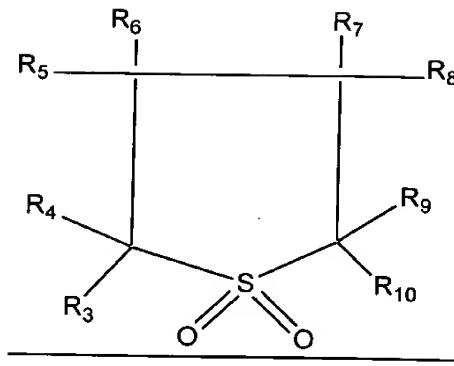
where R₃ - R₁₀ are independently H or an alkyl group, and and from about 0.1 to about 15 percent by weight of a basic amine compound.

Claims 14-19 (canceled).

Claim 20 (currently amended). A method of removing a photoresist coating from a substrate using the composition of claim 14 a composition comprising from about 0.01 percent by weight to about 10 percent by weight of ammonium hydrogen fluoride, from about 15 percent by weight to about 50 percent by weight and water, from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:

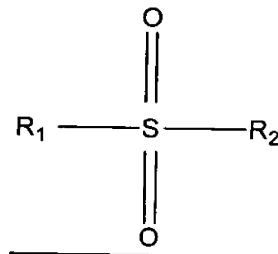


where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:

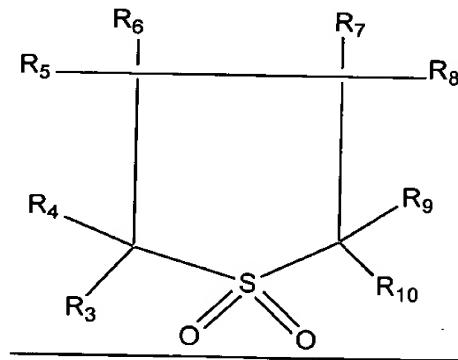


where R₃ - R₁₀ are independently H or an alkyl group.

Claim 21 (currently amended). A method of removing etch residue from a substrate using the composition of claim 14 a composition comprising from about 0.01 percent by weight to about 10 percent by weight of ammonium hydrogen fluoride, from about 15 percent by weight to about 50 percent by weight water, from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:



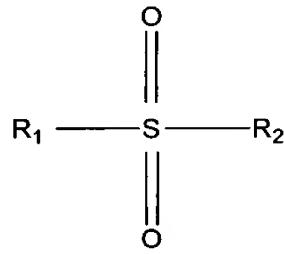
where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:



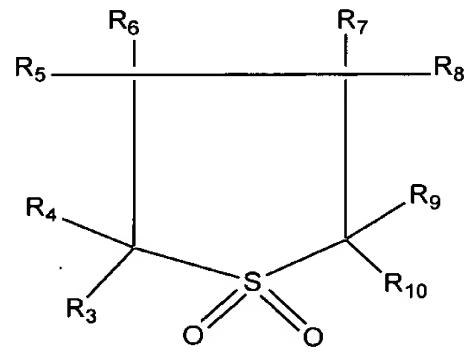
where R₃ - R₁₀ are independently H or an alkyl group.

Claim 22 (currently amended). A method of etching silicon oxide using the composition of claim 14 a composition comprising from about 20 percent by weight to about

40 percent by weight of one or more fluoride compounds selected from the group consisting of ammonium hydrogen fluoride and ammonium bifluoride, from about 15 percent by weight to about 50 percent by weight water, and from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide corresponding to the following:



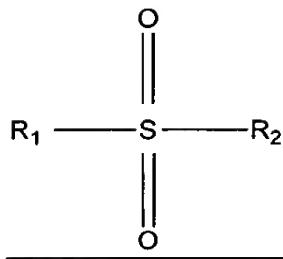
where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl, or a sulfone solvent corresponding to the following:



where R₃ - R₁₀ are independently H or an alkyl group, and a co-solvent.

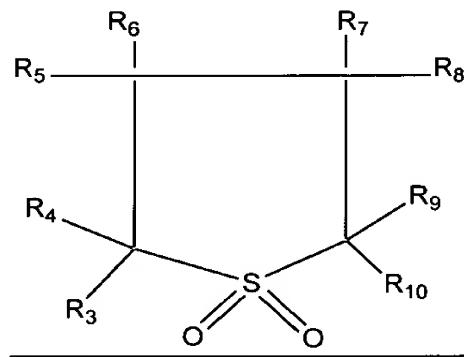
Claims 23-30 (canceled).

Claim 31 (currently amended). A method of etching silicon oxide using the composition of claim 23 a composition comprising from about 20 percent by weight to about 40 percent by weight of one or more fluoride compounds, from about 15 percent by weight to about 50 percent by weight water and from about 10 percent by weight to about 95 percent by weight of a compound which is either an organic sulfoxide solvent corresponding to the following:



where R₁ and R₂ are H, OH or an alkyl, at least one of R₁ and R₂ is an alkyl

or sulfone solvent corresponding to the following:



where R₃ - R₁₀ are independently H or an alkyl group.

Claim 32 (new). The method of claim 12 wherein the co-solvent is present in an amount from about 0.1 to about 60 percent by weight.

Claim 33 (new). The composition of claim 12 wherein said fluoride compound is ammonium hydrogen fluoride and said organic sulfoxide is dimethylsulfoxide.

Claim 34 (new). The method of claim 12 wherein said fluoride compound is ammonium bifluoride and said organic sulfoxide is dimethylsulfoxide.

Claim 35 (new). The method of claim 12 further comprising a chelating agent selected from the group consisting of gallic acid, catechol, tetrabutyl phosphonium hydroxide and dicarbethoxyhydrazine.

Claim 36 (new). The method of claim 21 wherein the composition further contains a co-solvent selected from the group consisting of acetic acid, methyl acetate, methyl lactate, ethyl acetate, ethylene glycol diacetate, ethyl lactate, propylene glycol, propylene carbonate, N-methyl pyrrolidone, methoxyethoxyethanol and polyethylene glycol monolaurate.

Claim 37 (new). The method of claim 21 wherein the composition further contains a basic amine compound selected from the group consisting of hydroxylamine, hydrazine, 2-amino-2-ethoxy ethanol, monoethanolamine, diethylhydroxylamine, choline, tetramethylammonium formate, monoisopropanolamine, diethanolamine, and triethanolamine.

Claim 38 (new). The composition of claim 21 further comprising a chelating agent selected from the group consisting of gallic acid, catechol, tetrabutyl phosphonium hydroxide and dicarbethoxyhydrazine.

Claim 39 (new). The method of claim 21 wherein said co-solvent is ethyl lactate and is present in an amount from about 30 percent by weight to about 60 percent by weight.

Claim 40 (new). The method of claim 31 wherein said fluoride compound is ammonium bifluoride.

Claim 41 (new). The method of claim 31 wherein said fluoride compound is ammonium hydrogen fluoride.